

Abstract Submitted  
for the MAR12 Meeting of  
The American Physical Society

**Exceptionally Weak Electron-Phonon Coupling on the  
Surface of the Topological Insulator  $\text{Bi}_2\text{Se}_3$  - A Promise for  
Room Temperature Applications**<sup>1</sup> TONICA VALLA, Z.-H. PAN,

Brookhaven National Laboratory, A.V. FEDOROV, Lawrence Berkeley National Laboratory, D. GARDNER, Y.S. LEE, S. CHU, Massachusetts Institute of Technology — Gapless surface states on topological insulators are protected from elastic scattering on non-magnetic impurities which makes them promising candidates for low-power electronic applications. However, for wide-spread applications, these states should have to remain coherent at ambient temperatures. Here, we studied temperature dependence of the electronic structure and the scattering rates on the surface of a model topological insulator,  $\text{Bi}_2\text{Se}_3$ , by high resolution angle-resolved photoemission spectroscopy. We found an extremely weak broadening of the topological surface state with temperature and no anomalies in the state's dispersion, indicating exceptionally weak electron-phonon coupling. Our results demonstrate that the topological surface state is protected not only from elastic scattering on impurities, but also from scattering on low-energy phonons, suggesting that topological insulators could serve as a basis for room temperature electronic devices.

<sup>1</sup>supported by the US Department of Energy (DOE)

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Date submitted: 14 Dec 2011

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